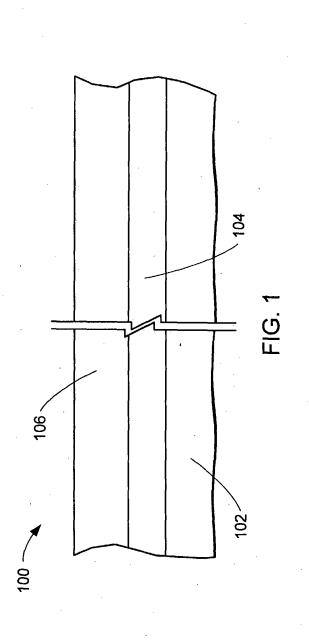
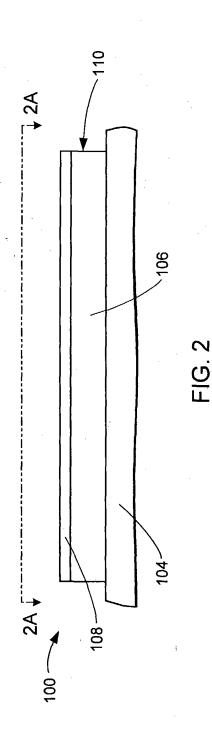
Title: THYISTOR-BASED SRAM AND METHOD USING QUASI-PLANAR FINFET PROCESS FOR THE FABRICATION THEREOF Inventors: Elgin Quek, et al. Docket No.:. 1016-027
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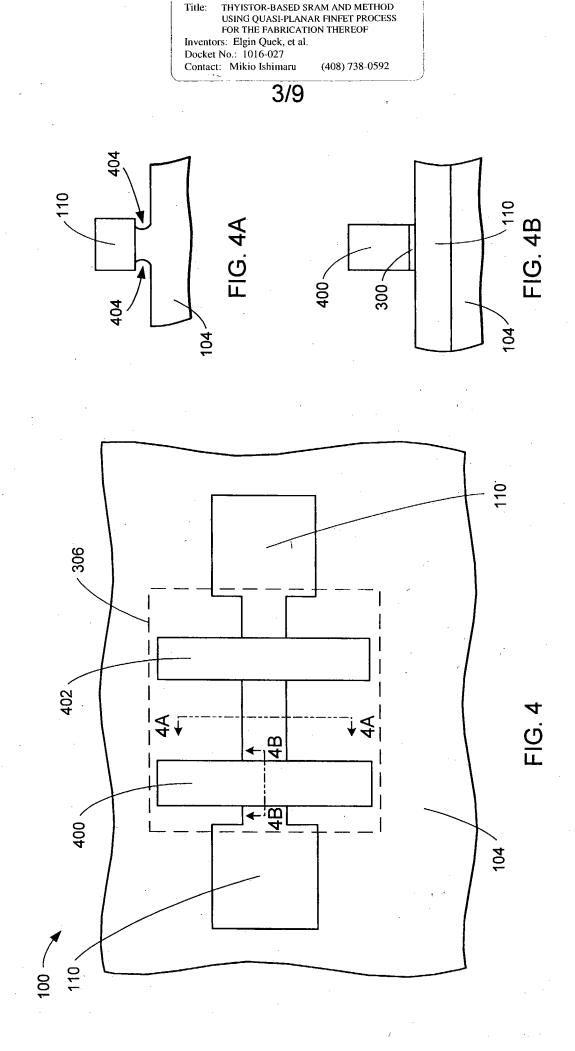




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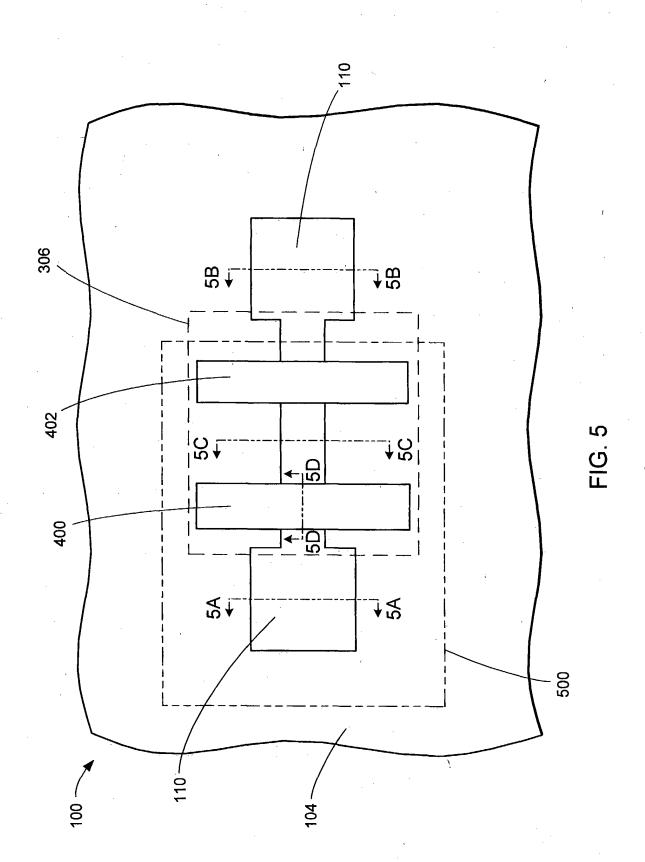
Docket No.: 1016-027

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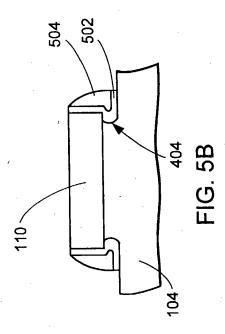


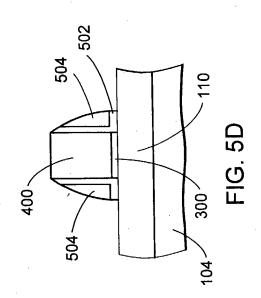
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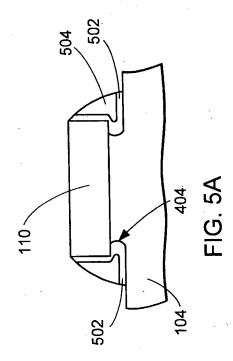
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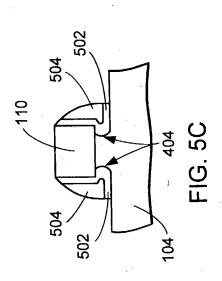


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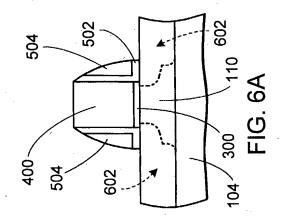


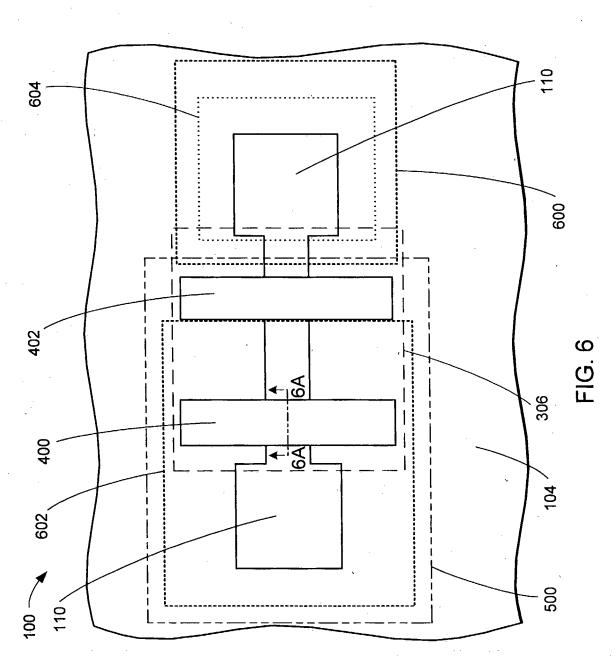


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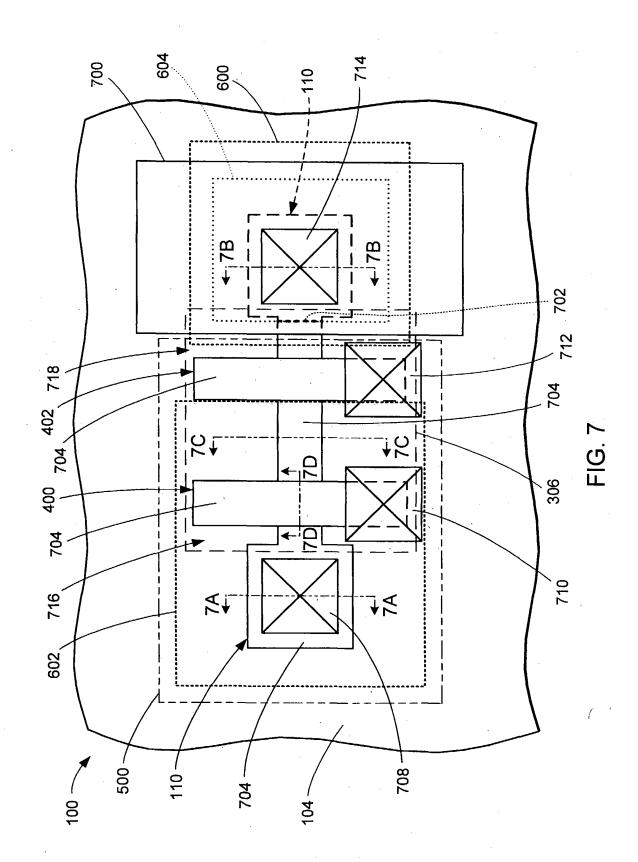




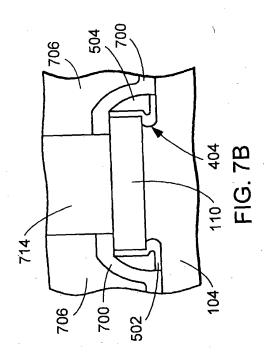
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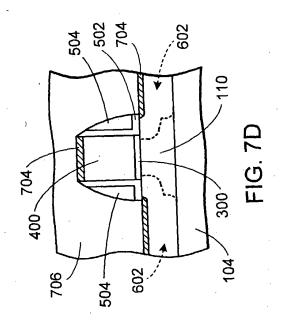
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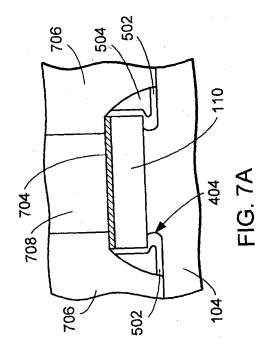
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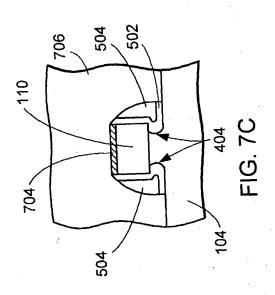


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